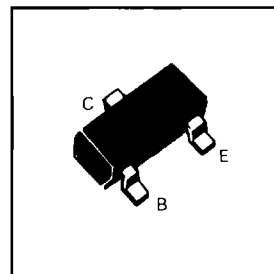


SOT23 PNP SILICON PLANAR SWITCHING TRANSISTORS

FMMT2907 FMMT2907A

PARTMARKING DETAILS:

FMMT2907 - 2B
FMMT2907A - 2F
FMMT2907R - 4P
FMMT2907AR - 5P



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	FMMT2907	FMMT2907A	UNIT
Collector-Base Voltage	V_{CB0}	-60	-60	V
Collector-Emitter Voltage	V_{CE0}	-40	-60	V
Emitter-Base Voltage	V_{EB0}	-5	-5	V
Continuous Collector Current	I_C	-600	-600	mA
Power Dissipation at $T_{amb} = 25^\circ\text{C}$	P_{TOT}	330	330	mW
Operating and Storage Temperature Range	$t_j:tstg$	-55 to +150		$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ unless otherwise stated)

PARAMETER	SYMBOL	FMMT2907		FMMT2907A		UNIT	CONDITIONS
		MIN.	MAX.	MIN.	MAX.		
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-40		-60		V	$I_C = -10\text{mA}$, $I_B = 0^*$
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-60		-60		V	$I_C = -10\mu\text{A}$, $I_E = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		-5		V	$I_E = -10\mu\text{A}$, $I_C = 0$
Collector-Emitter Cut-Off Current	I_{CEX}		-50		-50	nA	$V_{CE} = -30\text{V}$, $V_{BE} = -0.5\text{V}$
Collector-Base Cut-Off Current	I_{CBO}		-20 -20		-10 -10	nA μA	$V_{CB} = -50\text{V}$, $I_E = 0$ $V_{CB} = -50\text{V}$, $I_E = 0$ $T_{amb} = 150^\circ\text{C}$
Base Cut-Off Current	I_B		-50		-50	nA	$V_C = -30\text{V}$, $V_B = -0.5\text{V}$
Static Forward Current Transfer Ratio	H_{FE}	35 50 75 100 30	300	75 100 100 100 50	300		$I_C = -0.1\text{mA}$, $V_{CE} = -10\text{V}$ $I_C = -1\text{mA}$, $V_{CE} = -10\text{V}$ $I_C = -10\text{mA}$, $V_{CE} = -10\text{V}$ $I_C = 150\text{mA}$, $V_{CE} = -10\text{V}^*$ $I_C = -500\text{mA}$, $V_{CE} = -10\text{V}^*$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.4 -1.6		-0.4 -1.6	V V	$I_C = -150\text{mA}$, $I_B = -15\text{mA}^*$ $I_C = -500\text{mA}$, $I_B = -50\text{mA}^*$
Base-Emitter	$V_{BE(sat)}$		-1.3 -2.6		-1.3 -2.6	V V	$I_C = -150\text{mA}$, $I_B = -15\text{mA}^*$ $I_C = -500\text{mA}$, $I_B = -50\text{mA}^*$
Transition Frequency	f_T	200		200		MHz	$I_C = -50\text{mA}$, $V_{CE} = -20\text{V}$ $f = 100\text{MHz}$
Output Capacitance	C_{obo}		8		8	pF	$V_{CB} = -10\text{V}$, $I_E = 0$ $f = 100\text{kHz}$
Input Capacitance	C_{ibo}		30		30	pF	$V_{BE} = -2\text{V}$, $I_C = 0$ $f = 100\text{kHz}$

* Measured under pulsed conditions. Pulse width = 200 μs . Duty cycle = 1%.

SWITCHING CHARACTERISTICS (at 25°C ambient temperature)

PARAMETER	SYMBOL	TYP.	MAX.	UNIT	CONDITIONS
Turn-On Time	t_{on}	26	50	ns	$V_{CC} = -30V$, $I_C = -150mA$ $I_{B1} = -15mA$ (See fig. 1)
Turn-Off Time	t_{off}	70	110	ns	$V_{CC} = -6V$, $I_C = -150mA$ $I_{B1} = -I_{B2} = -15mA$ (See Fig. 2)

CIRCUITS FOR MEASURING SWITCHING TIMES

